

isc Silicon NPN Power Transistor

2SC3992

DESCRIPTION

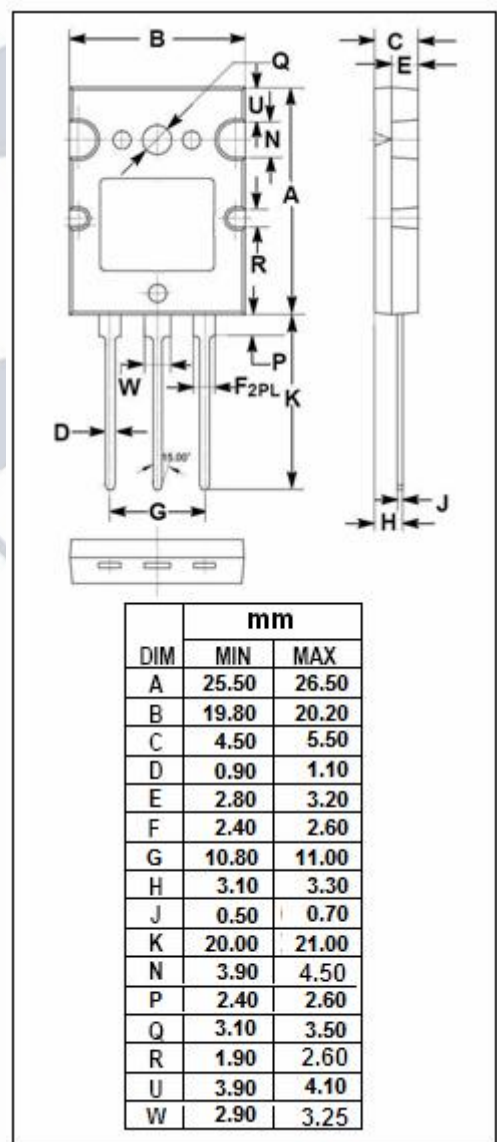
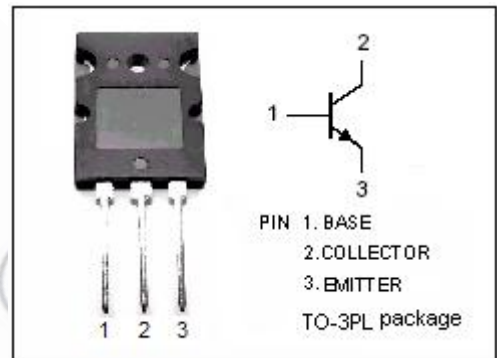
- High Switching Speed
- High Breakdown Voltage-
: $V_{(BR)CBO} = 1100V(\text{Min})$

APPLICATIONS

- Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1100	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	12	A
I_{CM}	Collector Current-Pulse	30	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	200	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEX(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=10\text{mA}; I_B=0$	800			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; R_{BE}=\infty$	1100			
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; I_B=0$	800			
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	7			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=800\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	μA
h_{FE-1}	DC Current Gain	$I_C=0.8\text{A}; V_{CE}=5\text{V}$	10		60	
h_{FE-2}	DC Current Gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	8			
T_{on}	On Time				0.5	μs
t_{stg}	Storage Time	$V_{CC}=400\text{V}, I_{B1}=-2.5\text{I}_{B2}=I_C=8\text{A}, R_L=50\Omega$			3.0	μs
t_f	Fall Time				0.3	μs